

## Complementary 30 V (G-S) MOSFET

### PRODUCT SUMMARY

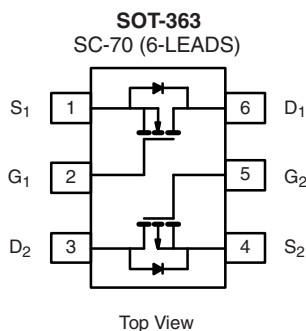
	V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
N-Channel	30	0.480 at V <sub>GS</sub> = 10 V	0.63
		0.700 at V <sub>GS</sub> = 4.5 V	0.52
P-Channel	- 30	0.940 at V <sub>GS</sub> = - 10 V	- 0.45
		1.700 at V <sub>GS</sub> = - 4.5 V	- 0.33

### FEATURES

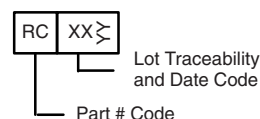
- TrenchFET® Power MOSFET
- Material categorization:  
For definitions of compliance please see  
[www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



Marking Code



**Ordering Information:** Si1539DL-T1-E3 (Lead (Pb)-free)  
Si1539DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V <sub>DS</sub>	30		- 30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20				
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	0.63	0.54	- 0.45	- 0.42	A
	T <sub>A</sub> = 85 °C		0.45	0.43	- 0.32	- 0.31	
Pulsed Drain Current		I <sub>DM</sub>	1				
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	0.25	0.23	- 0.25	- 0.23	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.30	0.27	0.30	0.27	W
	T <sub>A</sub> = 85 °C		0.16	0.14	0.16	0.14	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150				°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	360	415	°C/W
		400	460	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	300	350	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)								
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	N-Ch	1		2.6	V	
		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	P-Ch	- 1		- 2.6		
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	N-Ch P-Ch			± 100 ± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	N-Ch			1	μA	
		V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V	P-Ch			- 1		
		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	N-Ch			5		
		V <sub>DS</sub> = - 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	P-Ch			- 5		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	N-Ch	1			A	
		V <sub>DS</sub> ≤ - 5 V, V <sub>GS</sub> = - 10 V	P-Ch	- 1				
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.59 A	N-Ch		0.410	0.480	Ω	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 0.42 A	P-Ch		0.800	0.940		
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.2 A	N-Ch		0.600	0.700		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 0.2 A	P-Ch		1.500	1.700		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 0.59 A	N-Ch		0.75		S	
		V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 0.42 A	P-Ch		0.5			
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 0.23 A, V <sub>GS</sub> = 0 V	N-Ch		0.80	1.2	V	
		I <sub>S</sub> = - 0.23 A, V <sub>GS</sub> = 0 V	P-Ch		- 0.86	- 1.2		
Dynamic <sup>b</sup>								
Total Gate Charge	Q <sub>g</sub>	N-Channel V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.59 A	N-Ch P-Ch		0.86 0.90	1.4 1.4	nC	
Gate-Source Charge	Q <sub>gs</sub>		N-Ch P-Ch		0.24 0.21			
Gate-Drain Charge	Q <sub>gd</sub>	P-Channel V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 0.42 A	N-Ch P-Ch		0.08 0.17			
Turn-On Delay Time	t <sub>d(on)</sub>	N-Channel V <sub>DD</sub> = 15 V, R <sub>L</sub> = 30 Ω I <sub>D</sub> ≅ 0.5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 Ω	N-Ch P-Ch		5 4	10 10	ns	
Rise Time	t <sub>r</sub>		N-Ch P-Ch		8 8	15 15		
Turn-Off Delay Time	t <sub>d(off)</sub>		P-Channel V <sub>DD</sub> = - 15 V, R <sub>L</sub> = 30 Ω	N-Ch P-Ch		8 5		15 10
Fall Time	t <sub>f</sub>		I <sub>D</sub> ≅ - 0.5 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 6 Ω	N-Ch P-Ch		7 7		15 15
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 0.23 A, dI/dt = 100 A/μs	N-Ch		15	30		
		I <sub>F</sub> = - 0.23 A, dI/dt = 100 A/μs	P-Ch		20	40		

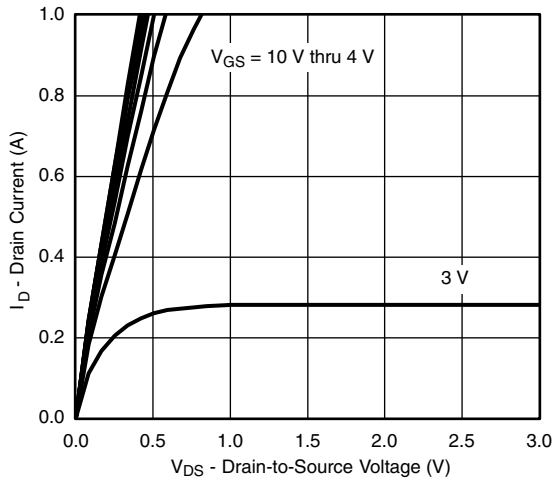
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

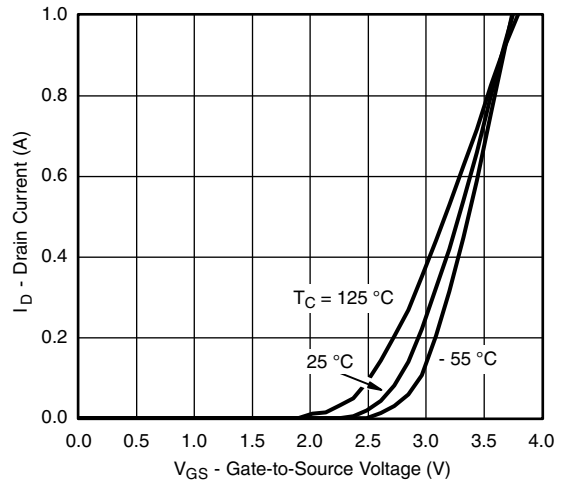
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

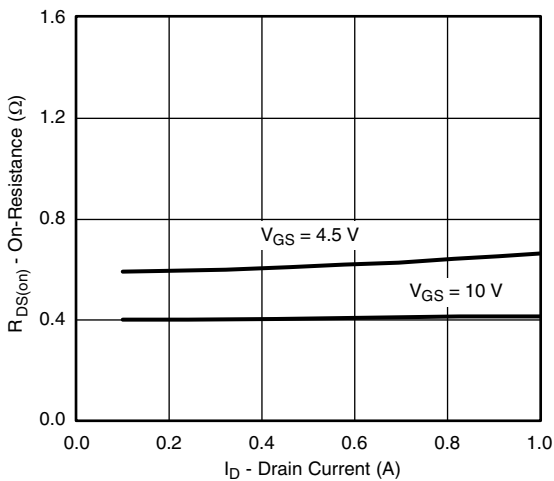
## N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



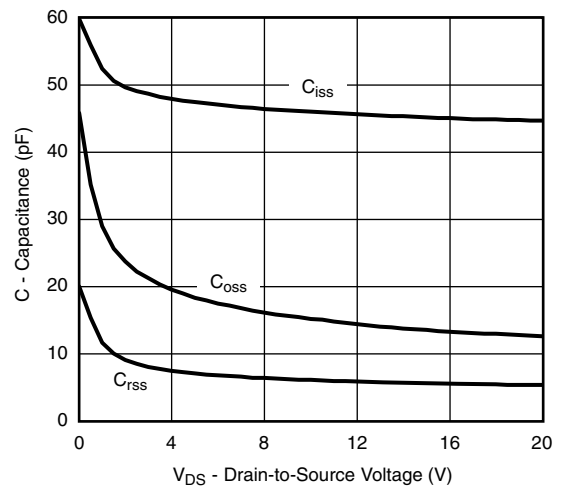
Output Characteristics



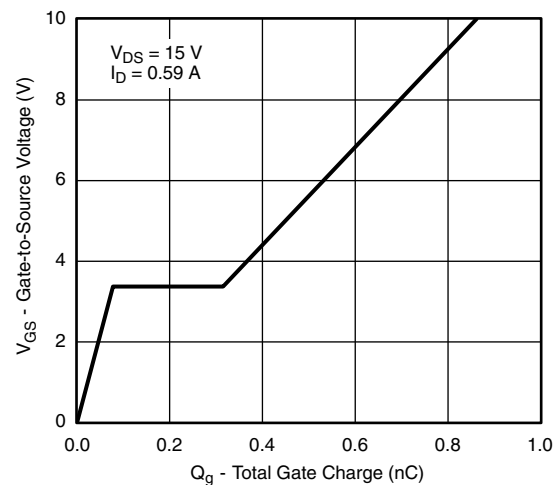
Transfer Characteristics



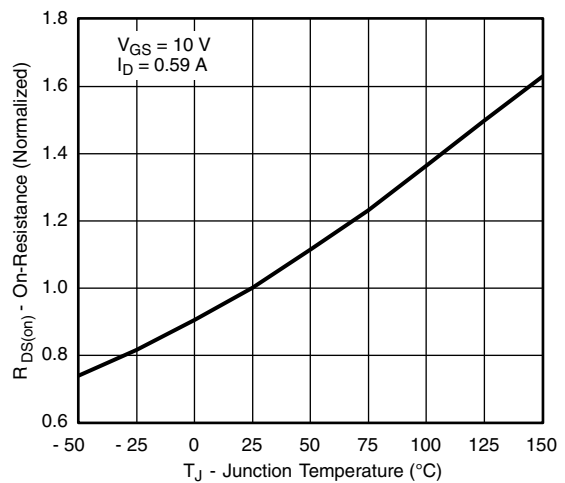
On-Resistance vs. Drain Current



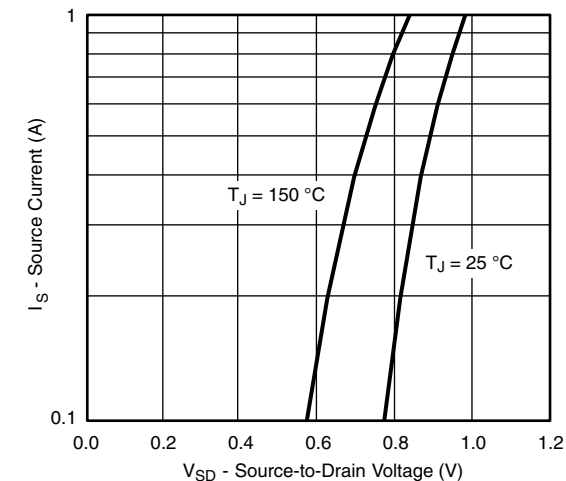
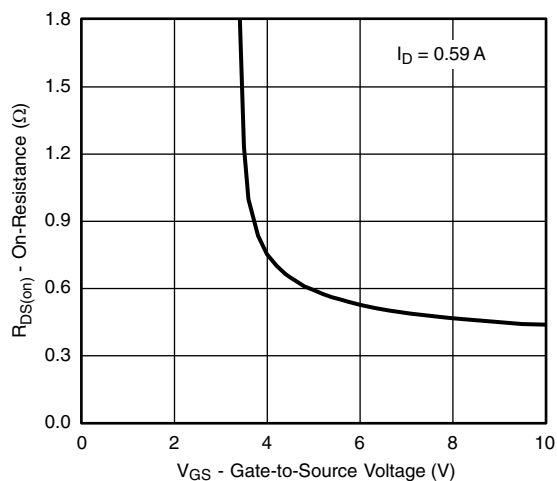
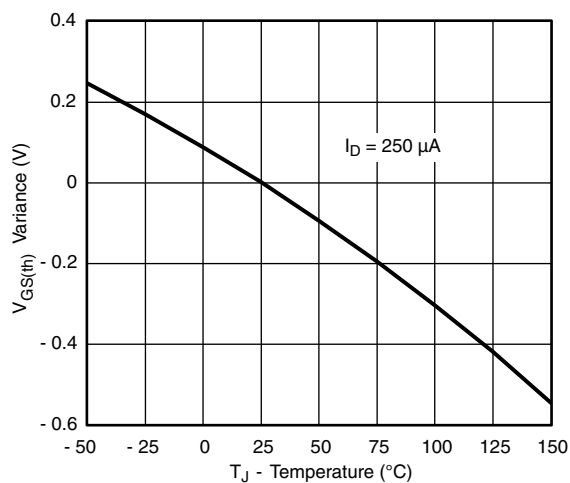
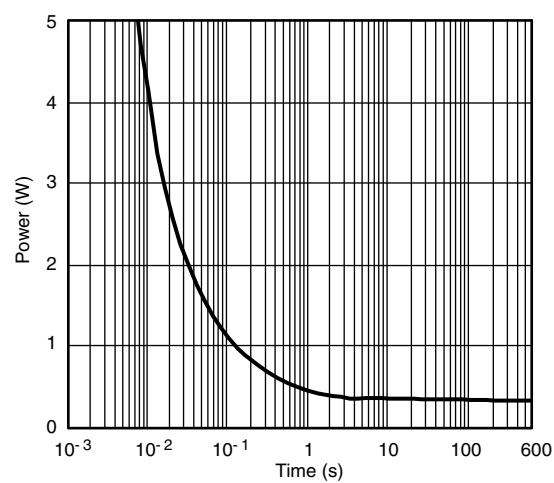
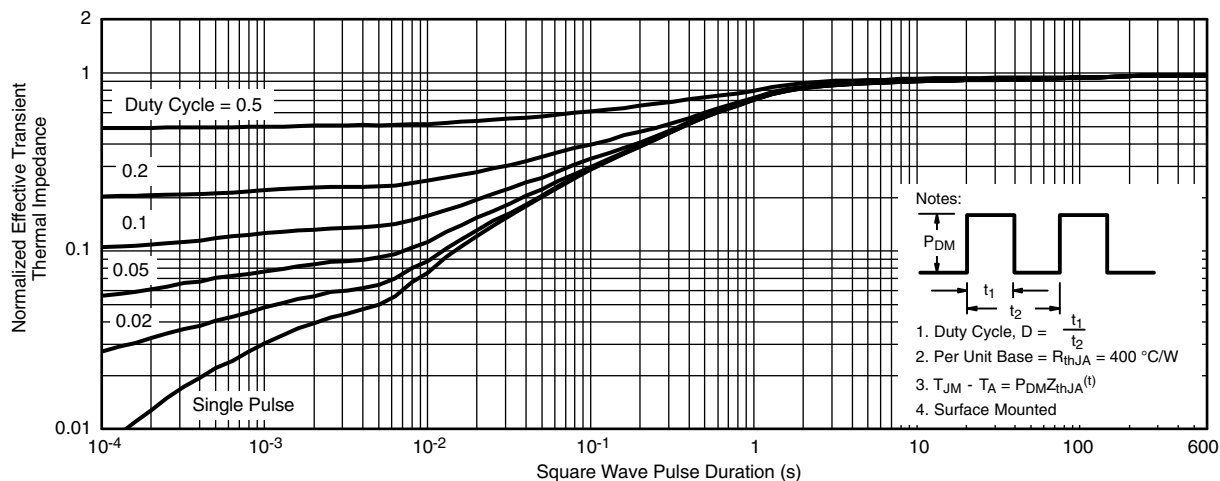
Capacitance



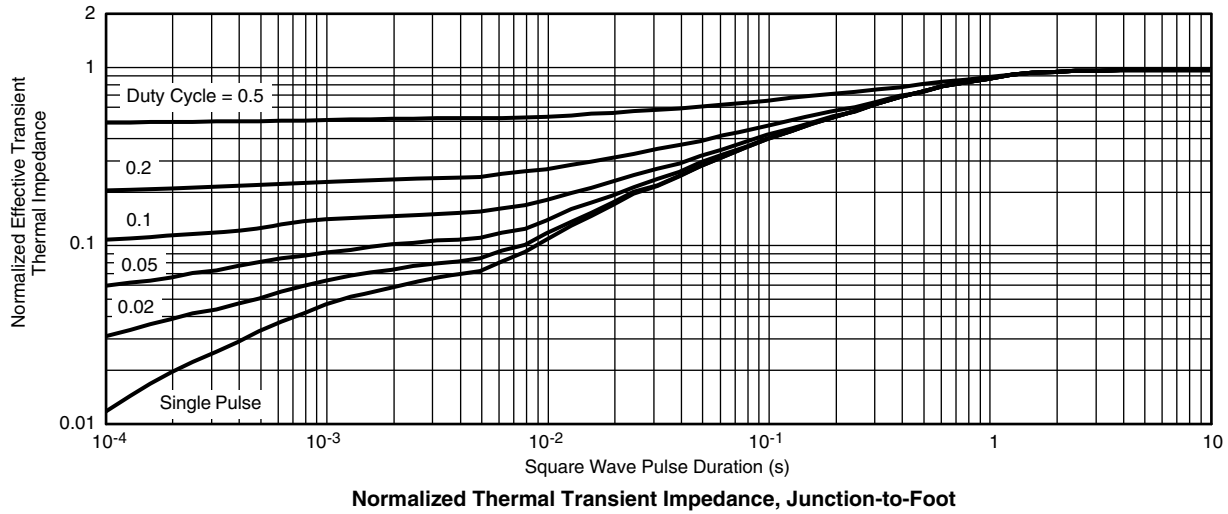
Gate Charge



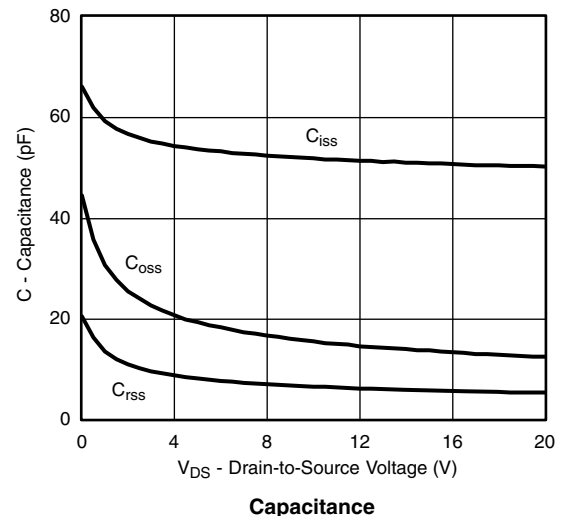
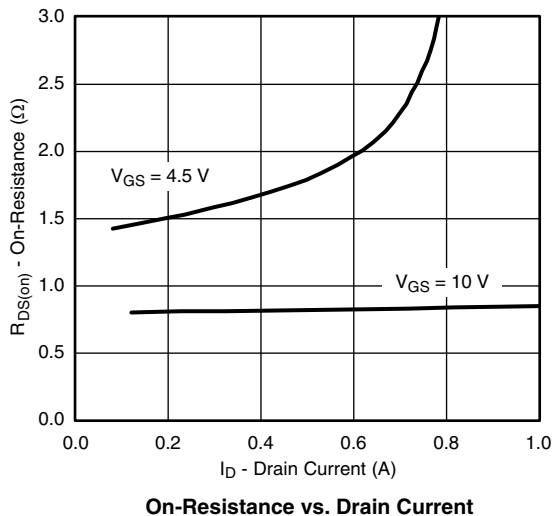
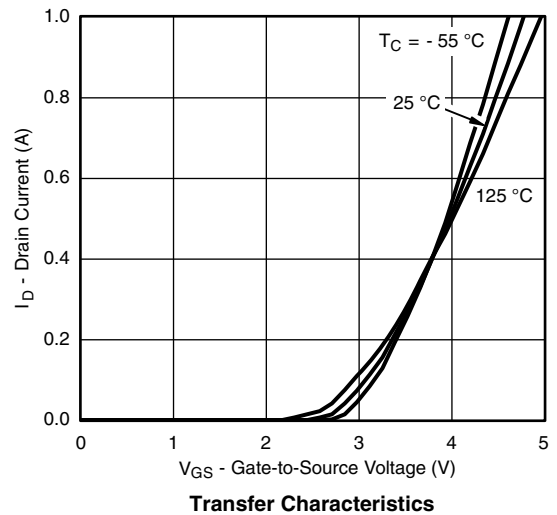
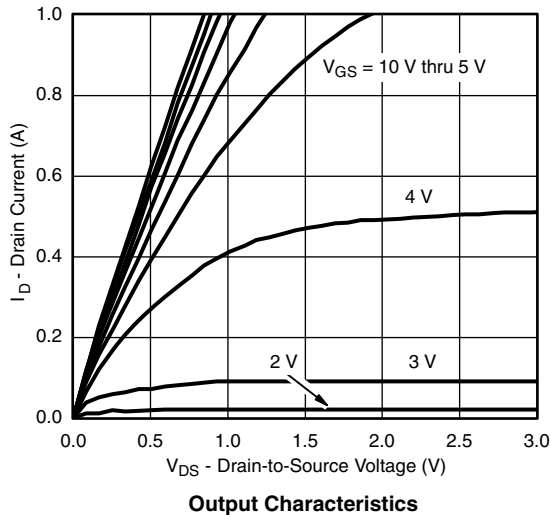
On-Resistance vs. Junction Temperature

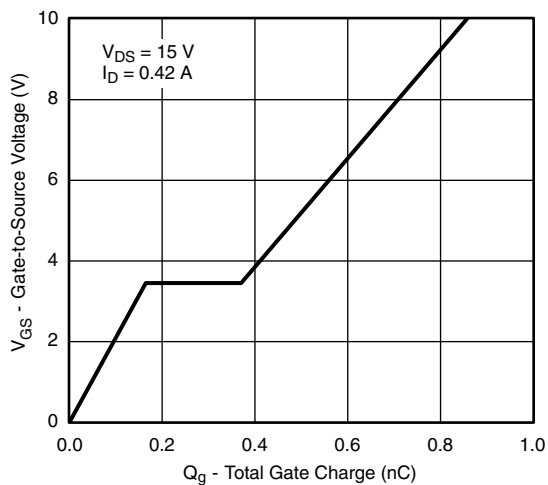
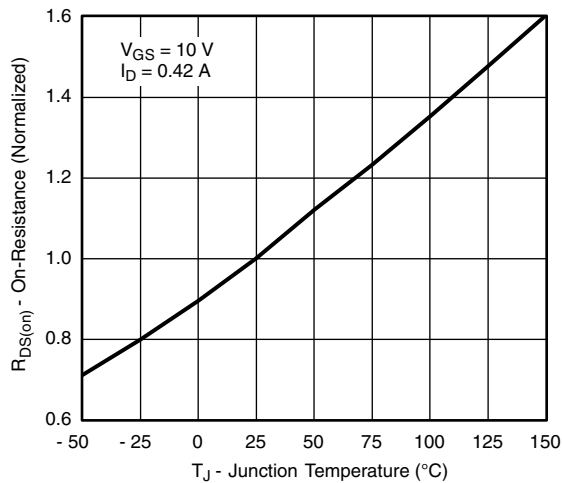
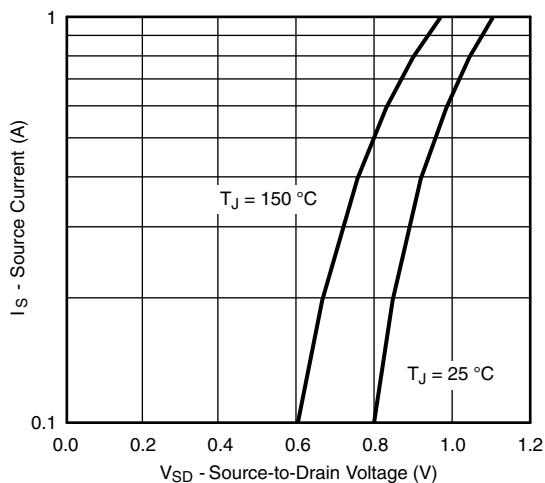
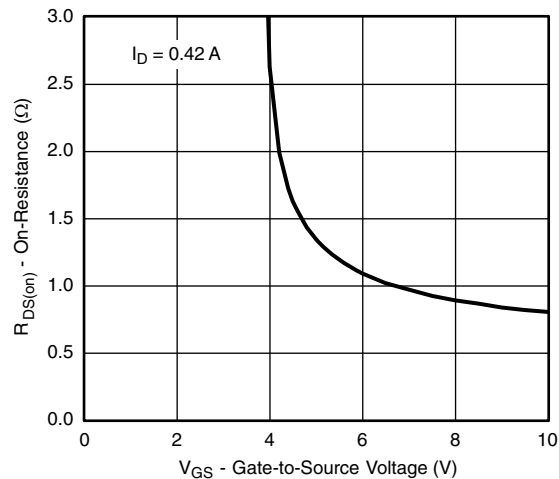
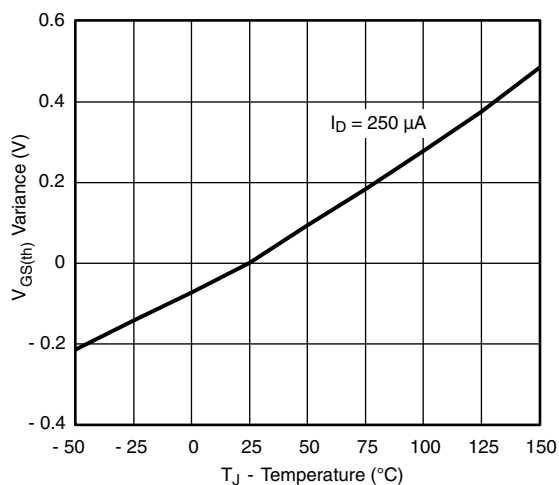
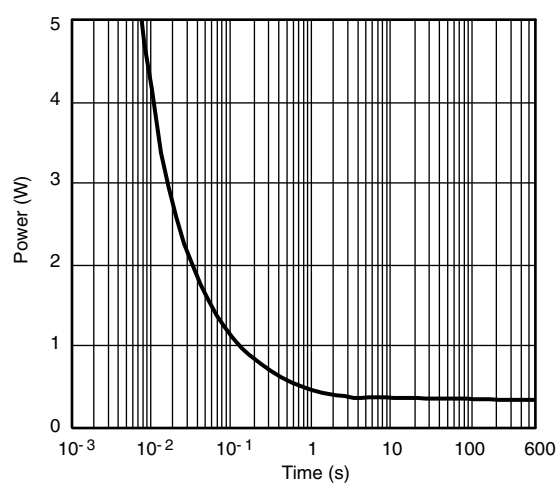
**N-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Normalized Thermal Transient Impedance, Junction-to-Ambient**

## N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

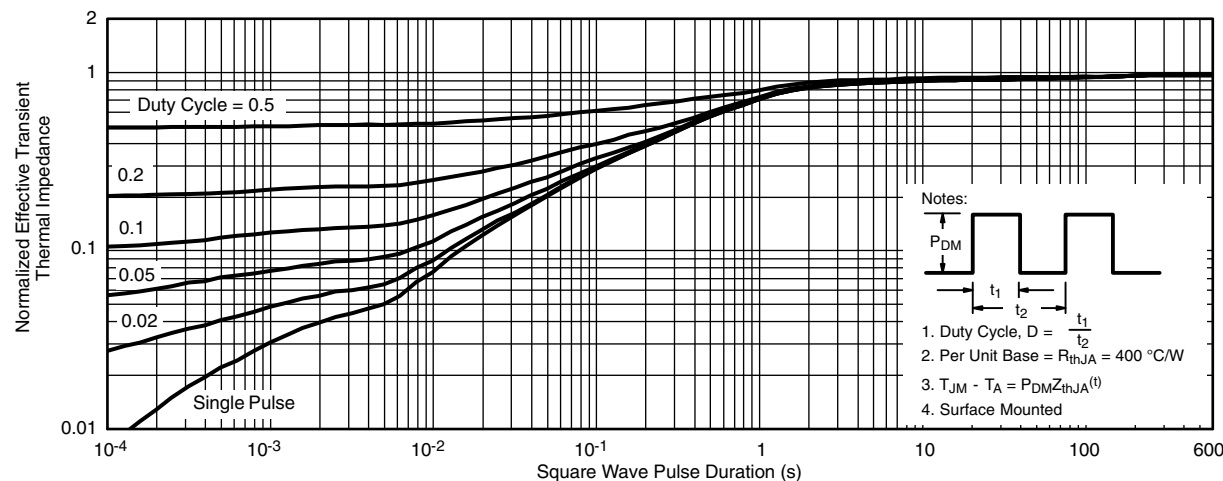


## P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

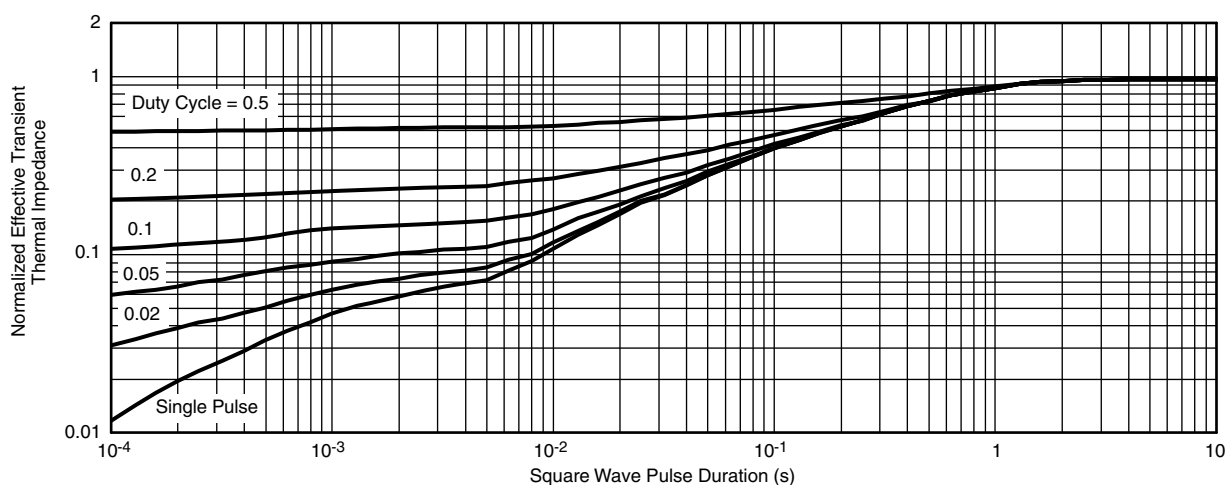


**P-CHANNEL TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power**

## P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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